# **PUA3117** (PU3117)

# Silicon NPN triple diffusion planar type

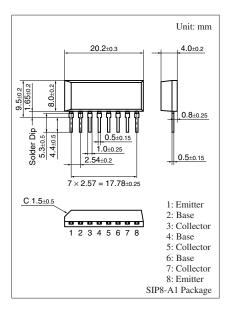
## For power amplification and switching

#### ■ Features

- High forward current transfer ratio hFE
- $\bullet$  Satisfactory linearity of forward current transfer ratio  $h_{\text{FE}}$
- NPN 3 elements

# ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector-base voltage (Emitter open)		V <sub>CBO</sub>	80	V	
Collector-emitter voltage (Base open)		V <sub>CEO</sub>	60	V	
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	6	V	
Collector current		$I_C$	3	A	
Peak collector current		$I_{CP}$	6	A	
Base current		$I_B$	1	A	
Collector power dissipation		P <sub>C</sub>	15	W	
T	$_{a} = 25^{\circ}C$		2.4		
Junction temperature		T <sub>j</sub>	150	°C	
Storage temperature		$T_{stg}$	-55 to +150	°C	

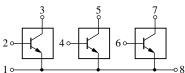


## ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

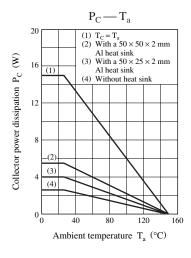
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 25 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 40 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 0.5 \text{ A}$	500		2 500	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 2 A, I_B = 0.05 A$			1.0	V
Transition frequency	$f_T$	$V_{CE} = 12 \text{ V}, I_{C} = 0.2 \text{ A}, f = 10 \text{ MHz}$		50		MHz

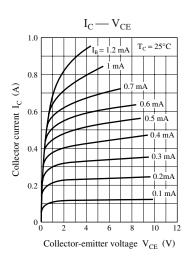
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

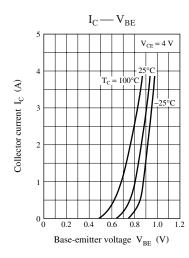
### ■ Internal Connection

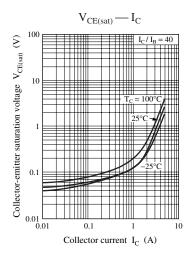


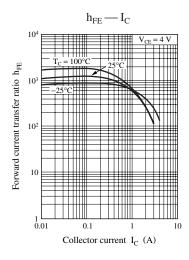
Note) The part number in the parenthesis shows conventional part number.

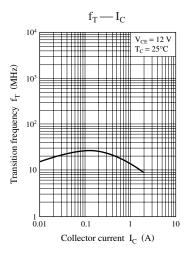


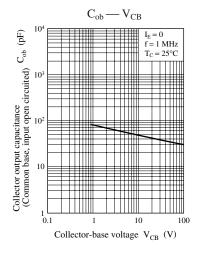


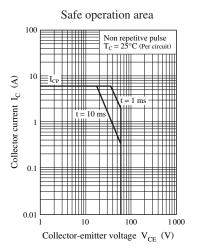












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